

ABSTRACT OF THE DISCLOSURE

A memory cell in which a variable resistive element and a Schottky diode are connected in series to each other. In a memory device, bit lines are arranged in a column direction, one end of the bit line is connected to a bit line decoder, and the other end thereof is connected to a reading circuit. Word lines are arranged in a row direction so as to intersect with the bit lines, and both ends of the word line are connected to word line decoders. In other words, the bit line and the word line are arranged in a matrix and a memory cell is located at a position where the bit line and the word line intersect with each other, which constitutes the memory device. An influence of a reading disturbance in the memory cell and the memory device is reduced.